



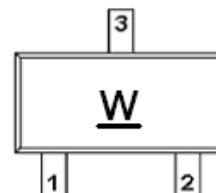
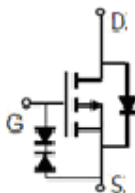
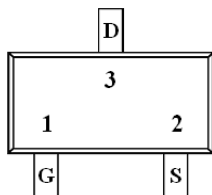
### General Description

AFP1033, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge. These devices are particularly suited for low voltage power management, such as smart phone and notebook computer, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- -30V/-0.6A,  $R_{DS(ON)} = 900 \text{ m}\Omega @ V_{GS} = -10\text{V}$
- -30V/-0.3A,  $R_{DS(ON)} = 1150 \text{ m}\Omega @ V_{GS} = -4.5\text{V}$
- -30V/-0.2A,  $R_{DS(ON)} = 1450 \text{ m}\Omega @ V_{GS} = -2.5\text{V}$
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- ESD Protected
- SOT-523 package design

### Pin Description ( SOT-523 )



### Application

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Smart Phones, Paggers

### Pin Define

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP1033ES52RG	<u>W</u>	SOT-523	Tape & Reel	3000 EA

※ AFP1033ES52RG : 7" Tape & Reel ; Pb- Free ; Halogen -Free



**Absolute Maximum Ratings**

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-30	V
Gate –Source Voltage	$V_{GSS}$	$\pm 12$	V
Continuous Drain Current( $T_J=150^{\circ}\text{C}$ )	$I_D$	$T_A=25^{\circ}\text{C}$	-0.6
		$T_A=70^{\circ}\text{C}$	-0.2
Pulsed Drain Current	$I_{DM}$	-1.0	A
Continuous Source Current(Diode Conduction)	$I_S$	-0.3	A
Power Dissipation	$P_D$	$T_A=25^{\circ}\text{C}$	0.27
		$T_A=70^{\circ}\text{C}$	0.16
Operating Junction Temperature	$T_J$	-55/150	$^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-55/150	$^{\circ}\text{C}$

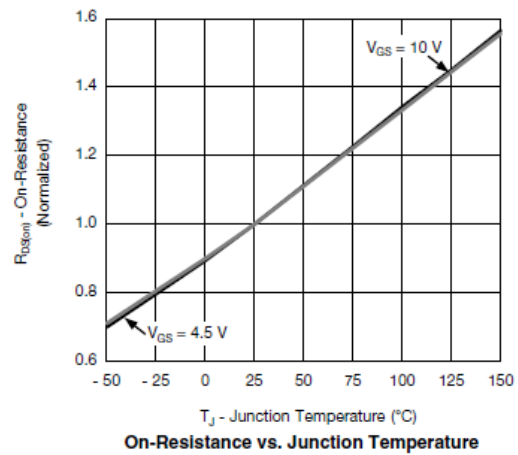
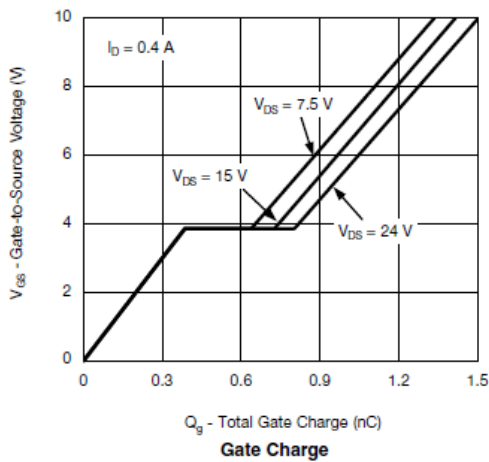
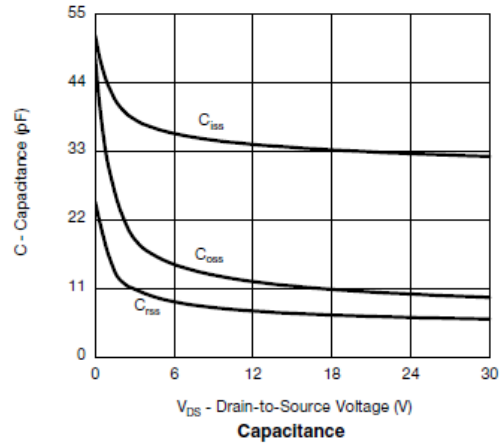
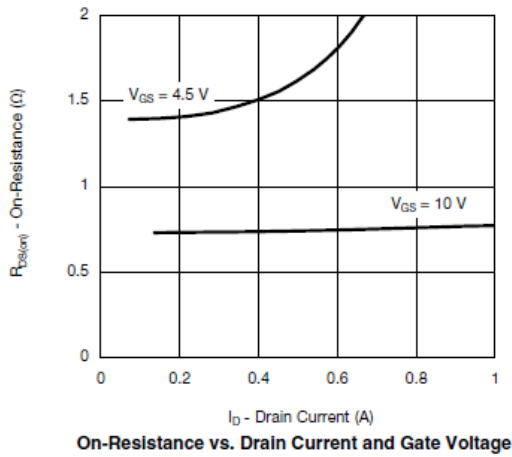
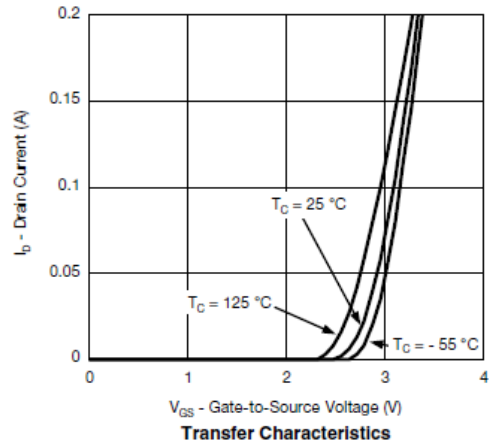
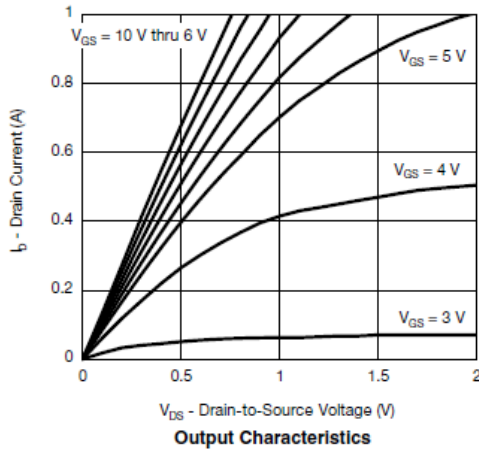
**Electrical Characteristics**

( $T_A=25^{\circ}\text{C}$  Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.7		-1.5	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 5$	mA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24V, V_{GS}=0V$			-1	uA
		$V_{DS}=-24V, V_{GS}=0V$ $T_J=85^{\circ}\text{C}$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	0.5			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-0.6A$		560	900	m $\Omega$
		$V_{GS}=-4.5V, I_D=-0.3A$		730	1150	
		$V_{GS}=-2.5V, I_D=-0.2A$		1000	1450	
Forward Transconductance	$g_{FS}$	$V_{DS}=-15V, I_D=-0.5A$		1		S
Diode Forward Voltage	$V_{SD}$	$I_S=-0.3A, V_{GS}=0V$		0.65	1.2	V
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=-15V, V_{GS}=0V$ $f=1\text{MHz}$		34		pF
Output Capacitance	$C_{oss}$			12		
Reverse Transfer Capacitance	$C_{rss}$			8		
Total Gate Charge	$Q_g$	$V_{DS}=-15V, V_{GS}=-4.5V$ $I_D \equiv -0.4A$		0.8	1.3	nC
Gate-Source Charge	$Q_{gs}$			0.4		
Gate-Drain Charge	$Q_{gd}$			0.4		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=38\Omega$ $I_D \equiv -0.2A, V_{GEN}=-4.5V$ $R_G=1\Omega$		35	50	ns
	$t_r$			20	30	
Turn-Off Time	$t_{d(off)}$			10	20	
	$t_f$			10	20	

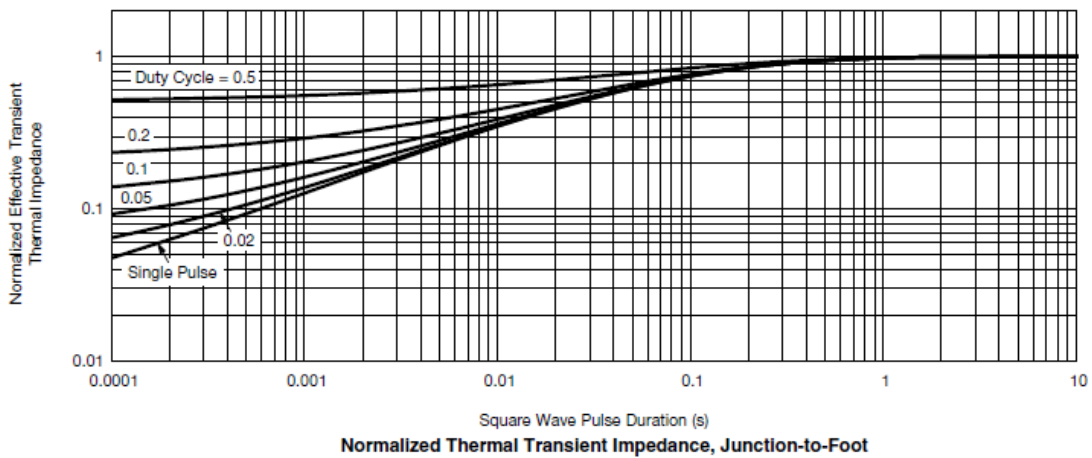
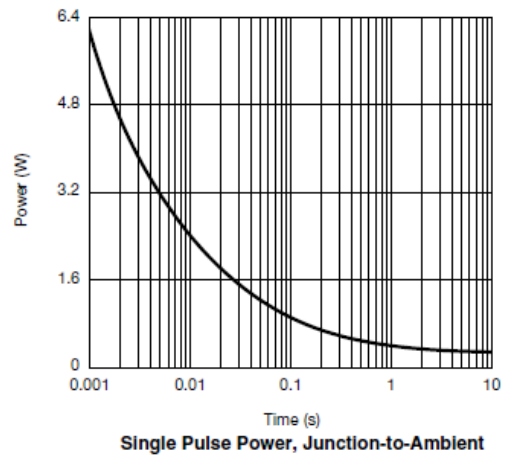
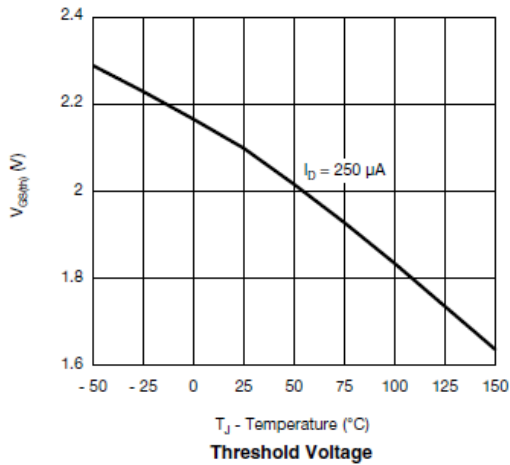
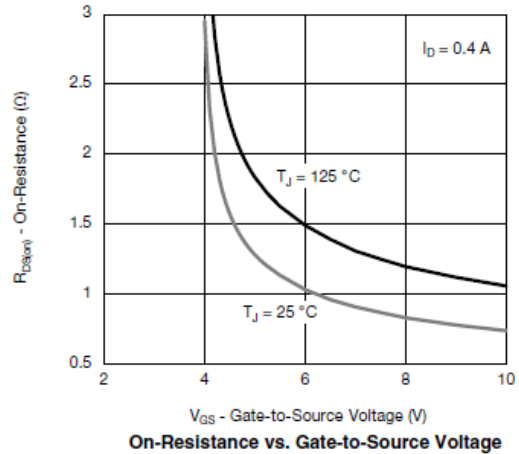
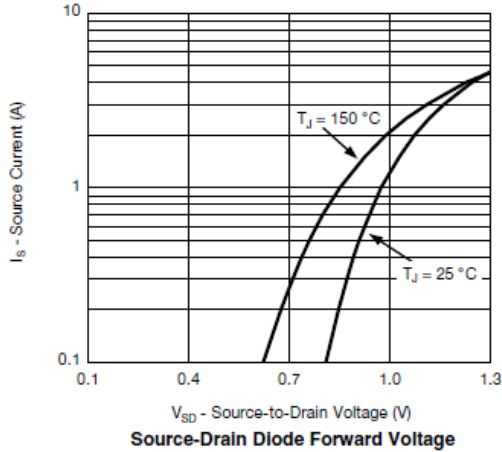


## Typical Characteristics





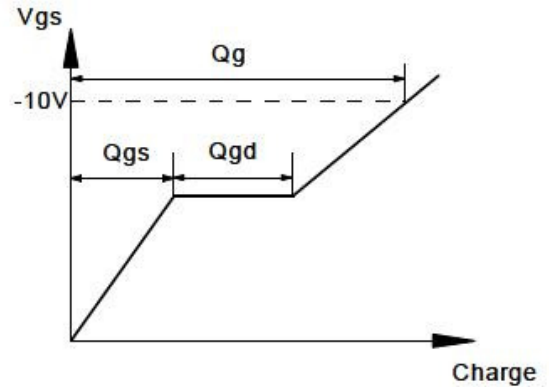
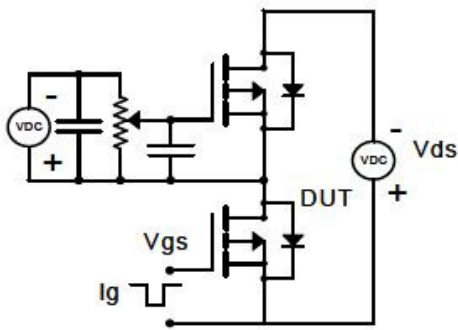
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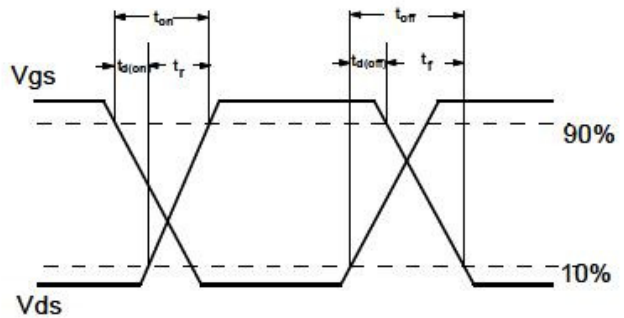
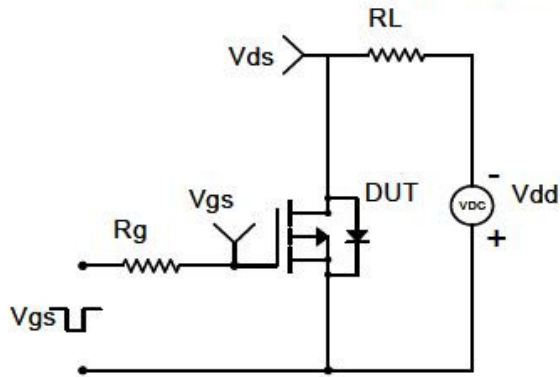


**Typical Characteristics**

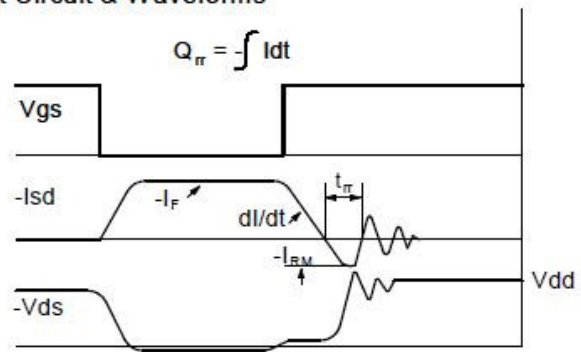
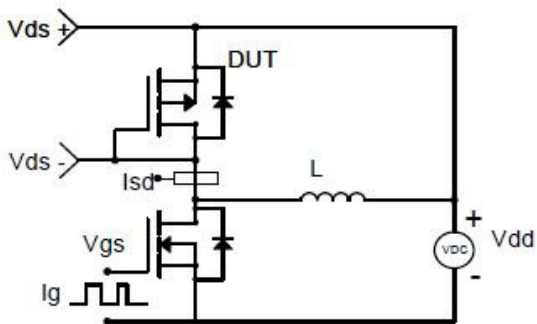
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

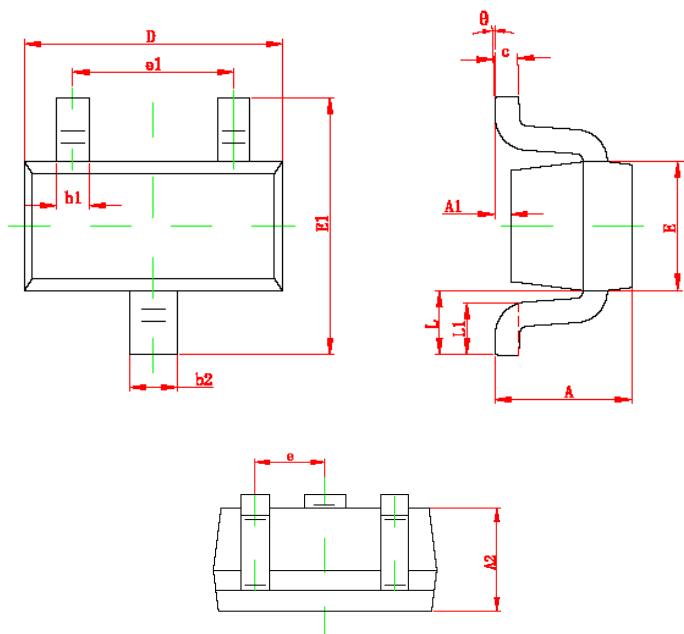


Diode Recovery Test Circuit & Waveforms





**Package Information ( SOT-523 )**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.325	0.010	0.013
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.750	0.850	0.030	0.033
E1	1.450	1.750	0.057	0.069
e	0.500 TYP		0.020 TYP	
e1	0.900	1.100	0.035	0.043
L	0.550 REF		0.022 REF	
L1	0.280	0.440	0.011	0.017
θ	0°	4°	0°	4°

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